

# ECE 302

## ELECTRONIC CIRCUITS

SPRING 2009

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<b>COURSE:</b>	M W F	9:10 - 10:00 am	Room 2243 EB
<b>CO &amp; PREREQ:</b>	ECE 303 & ECE 202 / 203		
<b>INSTRUCTOR:</b>	G.M. Wierzba	Room 3215 EB	355-5225; wierzba@msu.edu
<b>WEB SITE:</b>	www.egr.msu.edu/~wierzba		
<b>OFFICE HRS:</b>	Tu Th	4:15 - 5:15 pm	or by appointment
<b>TEXTS:</b>	G.M. Wierzba, <i>ECE 302 Course e-Notes, Spring 2009 Edition</i> , available at <a href="http://stores.lulu.com/willowepublishing">http://stores.lulu.com/willowepublishing</a>  Schubert & Kim, <i>Active and Non-Linear Electronics</i> , Wiley, 2004  M. Rashid, <i>Intro. To PSpice Using Orcad for Circuits and Electronics</i> , Pearson Prentice Hall, 2004		
<b>GRADING:</b>	Three one-hour exams	(2/9, 3/23, 4/13)	200 pts
	Final exam*	(Th., May 7, 7:45 - 9:45 am)	200 pts
	Homework *	(normalized)	50 pts
	<i>*You must obtain a passing grade to pass the course.</i>		
<b>POLICIES:</b>	You are expected to arrive for class on time. No laptop computers are allowed during class. No student can wear earphones during class		
<b>HOMEWORK:</b>	Homework is to be done on 8.5" x 11" paper using only one side. It must be stapled and ragged edges must be trimmed. Whenever possible, the correct answer is to be circled or boxed. You may work with other students (list all names below yours) but the work you submit must be done by you. Assignments which are identical will all receive a grade of <b>zero</b> . You must type and run all of your own computer work. Copying of old assignments or computer files will be dealt with severely.		
<b>OTHER:</b>	Only simple scientific calculators are allowed for exams. Exam questions have little or no partial credit. There are <b>NO MAKE UP EXAMS</b> . One 1-hour exam will be dropped in computing your grade. Late homework <b>WILL NOT</b> be accepted. Your lowest homework grade will be dropped in computing your normalized homework grade.		

***An 85% attendance rate is required to pass the course, that is, you can miss 7 classes. Please keep your own record of absences.***

## DETAILED TOPICS:

- Chapter 2: Diode Characteristics and Circuits
- 2.1 Basic Functional Requirements of an Ideal Diode  
Piecewise Linear Model, Transition Point, Assumed States for Analysis, Strategy for Guessing States
  - 2.2 Semiconductor Diode V-I Relationship  
Physics of the P-N Junction, Shockley Equation, Approximations, Dynamic Resistance
  - 2.3 Diode as a Circuit Element  
Transcendental Equation, SPICE Model Parameters, Software Curve Tracer, Effects of Temperature
  - 2.4 Load Lines  
Graphical Solutions to Static Circuits, Inspection Short Cut, Graphical Solutions of Circuits with Time-Varying Sources
  - 2.5 Simplified Piecewise Linear Model
  - 2.6 Diode Applications  
Positive Clipper with SPICE Evaluation, Negative Clipper with SPICE Evaluation, Double Clipper with SPICE Evaluation, Half-Wave Rectifier with SPICE Evaluation, Full-Wave Rectifier with SPICE Evaluation, Filtered Full-Wave Rectifier with SPICE Evaluation, Transformers, Peak Detectors, Clamping Circuits, Voltage Multiplier, Or-Gate, And-Gate
  - 2.7 Zener Diode and Applications  
Piecewise Linear Model, Shunt Regulator, Design - Cigarette Lighter Adapter for a CD Player, SPICE Evaluation
- Chapter 3: Bipolar Junction Transistor (BJT) Characteristics
- 3.1 BJT V-I Relationships  
NPN BJT, Physical Operation in the Active Region, Physical Operation in the Cut-Off Region, Physical Operation in the Saturation Region, Physical Operation in the Inverse-Active Region, PNP BJT, Ebers-Moll Equations, SPICE Model Parameters, Software Curve Tracer
  - 3.4 Modeling of the BJT in its Regions of Operation  
Active, Saturation, Cut-Off, Inverse-Active, Inverse-Saturated, Inverse Cut-Off, Edge-of-Saturation, Edge-of-Cut-Off, Edge-of-Saturation Reverse, Edge-of-Cut-Off-Reverse
  - 3.2 The BJT as a Circuit Element  
Assumed States Analysis, Strategies for Guessing the State of an NPN (PNP) BJT, Load-Line Approach, Ebers-Moll Approach
  - 3.6 Biasing the BJT  
Fixed Bias Circuit, Emitter Bias Circuit with Two Supplies, Emitter Bias Circuit with One Supply, Emitter Bias Circuit Design, Biasing PNP Transistors
  - 3.5 Digital Electronic Applications  
Resistor-Transistor Logic Gates, Logic Level Diagram, Fanout, Nor-Gate, Step Response of an RL (RC) Circuit, Switching Inductive Loads, Damping Diode, SPICE Evaluation, Switching Capacitive Loads, SPICE Evaluation

- Chapter 5: Single Transistor Amplifiers
  - 5.2 BJT Low-Frequency Models
    - Definition of Small Signal, Small-Signal Analysis Algorithm Small-Signal Model for an NPN, PNP BJT and a diode
  - 5.3 Common-Emitter Amplifier
    - Voltage Gain, Input Impedance, Current Gain, Power Gain, Output Impedance, SPICE Verification
  - 5.4 Common-Collector (Emitter Follower) Amplifier
    - Voltage Gain, Input Impedance, Current Gain, Power Gain, Output Impedance
  - 5.5 Common-Base Amplifier
    - Voltage Gain, Input Impedance, Current Gain, Power Gain, Output Impedance
  
- Chapter 6: Multiple-Transistor Amplifiers
  - 6.1 Using Simple Stages Cascaded
    - Common-Emitter Common-Emitter Amplifier
  
- Chapter 10: Frequency Response of Transistor Amplifiers
  - 10.X Departure from Ideal Diode Performance
    - Depletion Capacitance, Diffusion Capacitance, SPICE Parameters of a Diode, AC Model of a Diode, SPICE Testing of V-I Characteristics
  - 10.Y Departure from Ideal Transistor Performance
    - SPICE Parameters of a BJT, AC Model of a BJT, SPICE Testing of V-I Characteristics, Measuring Low Frequency AC Parameters, AC Model for a BJT (Giacoletto Model)
  - 10.6 High-Frequency Amplifiers
    - Wideband Common-Emitter Amplifier, SPICE Evaluation, Short Circuit Time Constants, Open Circuit Time Constants, Loading Effects on Bandwidth
  
- Chapter 4: Field-Effect Transistor Characteristics
  - 4.1 Junction Field-Effect Transistors (JFETs)
    - N-Channel JFET, Physical Operation in Cut-Off and Ohmic Region, Physical Operation in Saturation, Character Curves and Equations, P-Channel JFET
  - 4.2 Metal-Oxide-Semiconductor Field-Effect Transistors (MOSFETs)
    - Enhancement N-Channel MOSFET, Physical Operation in Cut-Off and Ohmic Region, Physical Operation in Saturation, Character Curves and Equations, Enhancement P-Channel MOSFET, FET - BJT Analogy
  - 4.3 FET as a Circuit Element
    - JFET SPICE Model Parameters, Software Curve Tracer, MOSFET SPICE Model Parameters, Software Curve Tracer, The JFET as a Voltage-Controlled Resistance with SPICE Verification, The JFET as a Current Source with SPICE Verification
  - 4.6 Biasing the FET
    - Fixed-Bias Circuit, Self-Bias Circuit, Fixed-Plus Self-Bias Circuit

- 4.3 FET as a Circuit Element
  - NMOS Inverter with a Pull-Up Resistor, NMOS Inverter with Capacitive Loads, CMOS Inverter, SPICE Transfer Curves, CMOS NOR-Gate, CMOS NAND-Gate, CMOS Transmission- Gate, Bulk-Pin Potential
- 5.7 FET Low-Frequency Models
  - Definition of Small Signal, Small-Signal Analysis Algorithm, Small-Signal Model for an N- and P- Channel JEFT, Small-Signal Model for an N- and P- Channel MOSFET
- 5.8 The Common-Source Amplifier
  - Voltage Gain, Input Impedance, Current Gain, Power Gain, Output Impedance, Comparison of a Common-Source Amplifier and a Common-Emitter Amplifier
- 6.1 Using Simple Stages Cascaded
  - Broadband Amplifier: Common-Source Common-Base Amplifier
- Chapter 7: Power Amplifiers and Output Stages
  - 7.1 Power Amplifier Classification
    - Class A, Total Harmonic Distortion, SPICE Measurement, Efficiency
  - 7.3 Complementary Pair Power Booster (Class B Amplifier)
    - Efficiency, Distortion, SPICE Verification
  - 7.4 Class AB Power Amplifiers
    - 15-Watt Power Amplifier
  - 7.6 Thermal Considerations